

**General Description**

I

Ordering Information:**Absolute Maximum Ratings** $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	110	A
	$I_{D@TC=75}$	83	A
	$I_{D@TC=100}$	69	A
Pulsed Drain Current	I_{DM}	330	A
Total Power Dissipation	$P_D@TC=25$	85	W
Total Power Dissipation	$P_D@TA=25$	3.4	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	240	mJ



Body Diode Reverse Recovery Time	trr	$I_F=20A,$ $di/dt=100A/\mu s$		23		nS
Body Diode Reverse Recovery Charge	Qrr	$I_F=20A,$ $di/dt=100A/\mu s$		120		nC

Note:

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Fig.1 Gate-Charge Characteristics

Fig.2 Capacitance Characteristics

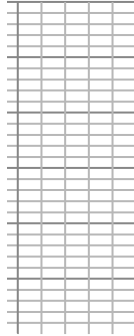


Fig.3 I

Fig.4 Typical output Characteristics

Fig.5

oltage V.S Junction Temperature

Fig.6 Resistance V.S Drain Current

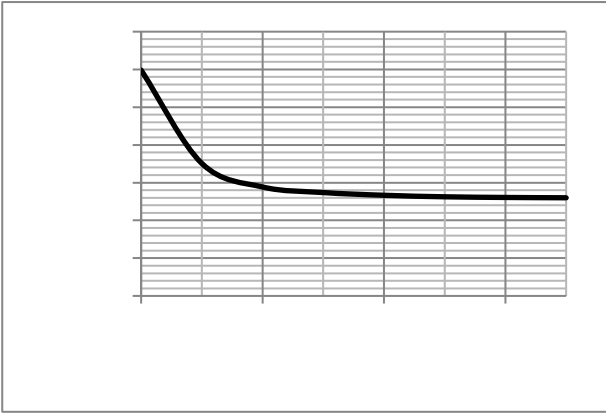


Fig.9 SOA Maximum Safe Operating Area

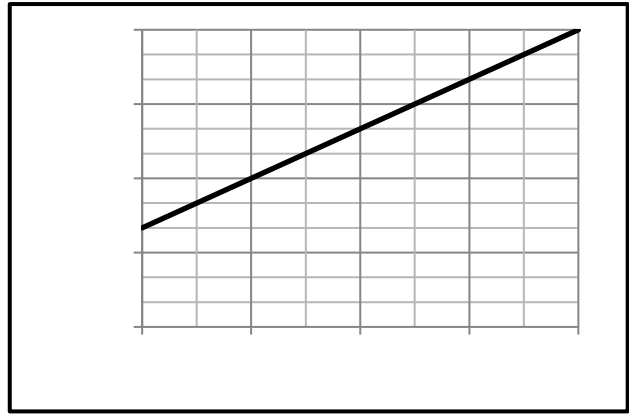


Fig.10 ID-Junction Temperature

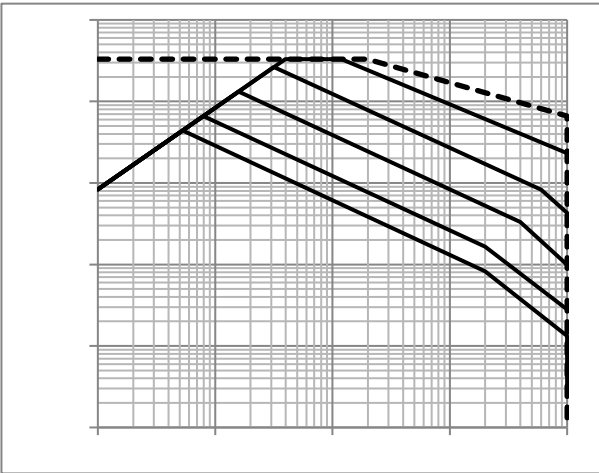


Fig.11 Switching Time Measurement Circuit

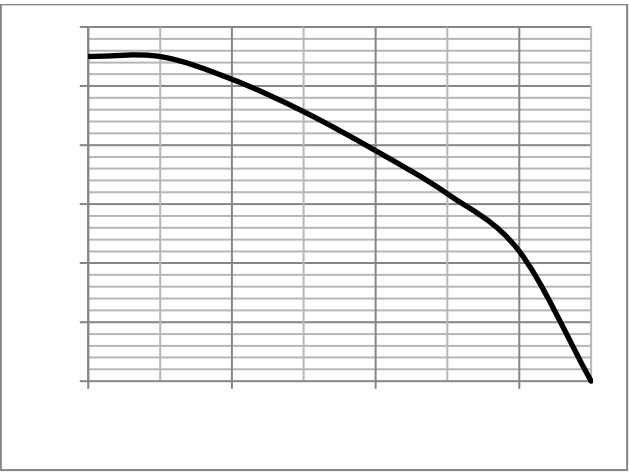


Fig.12 Gate Charge Waveform

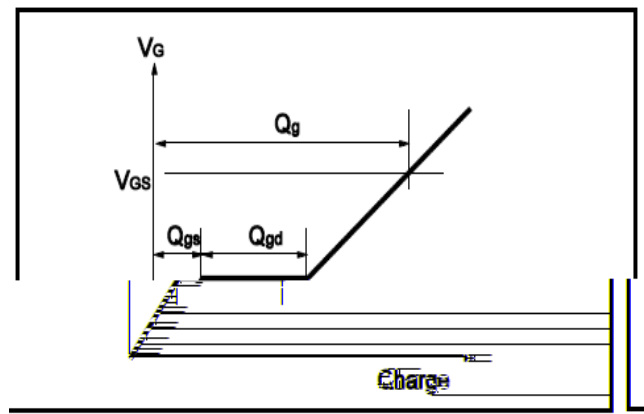
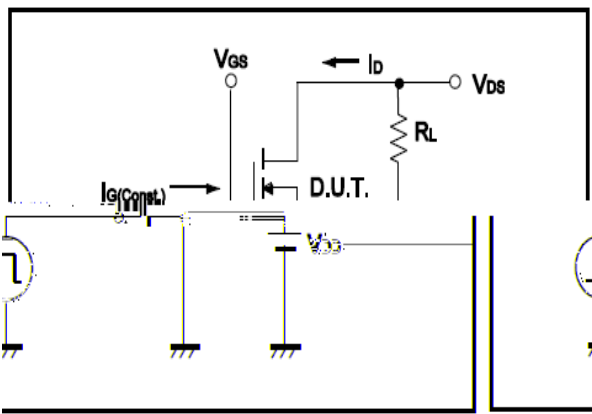




Fig.13 Switching Time Measurement Circuit

Fig.14 Gate Charge Waveform

